

/ Descriptions

TO-220F PNP Silicon PNP transistor in a TO-220F Plastic Package.

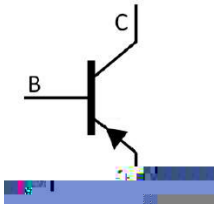
/ Features

h_{FE} f_T 2SC5248
Flat DC current gain characteristics, high breakdown voltage, high f_T , wide SOA, complements the 2SC5248.

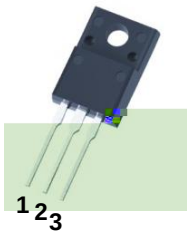
/ Applications

()
High-voltage switching(audio output amplifier transistor, stabilized power supply transistor).

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

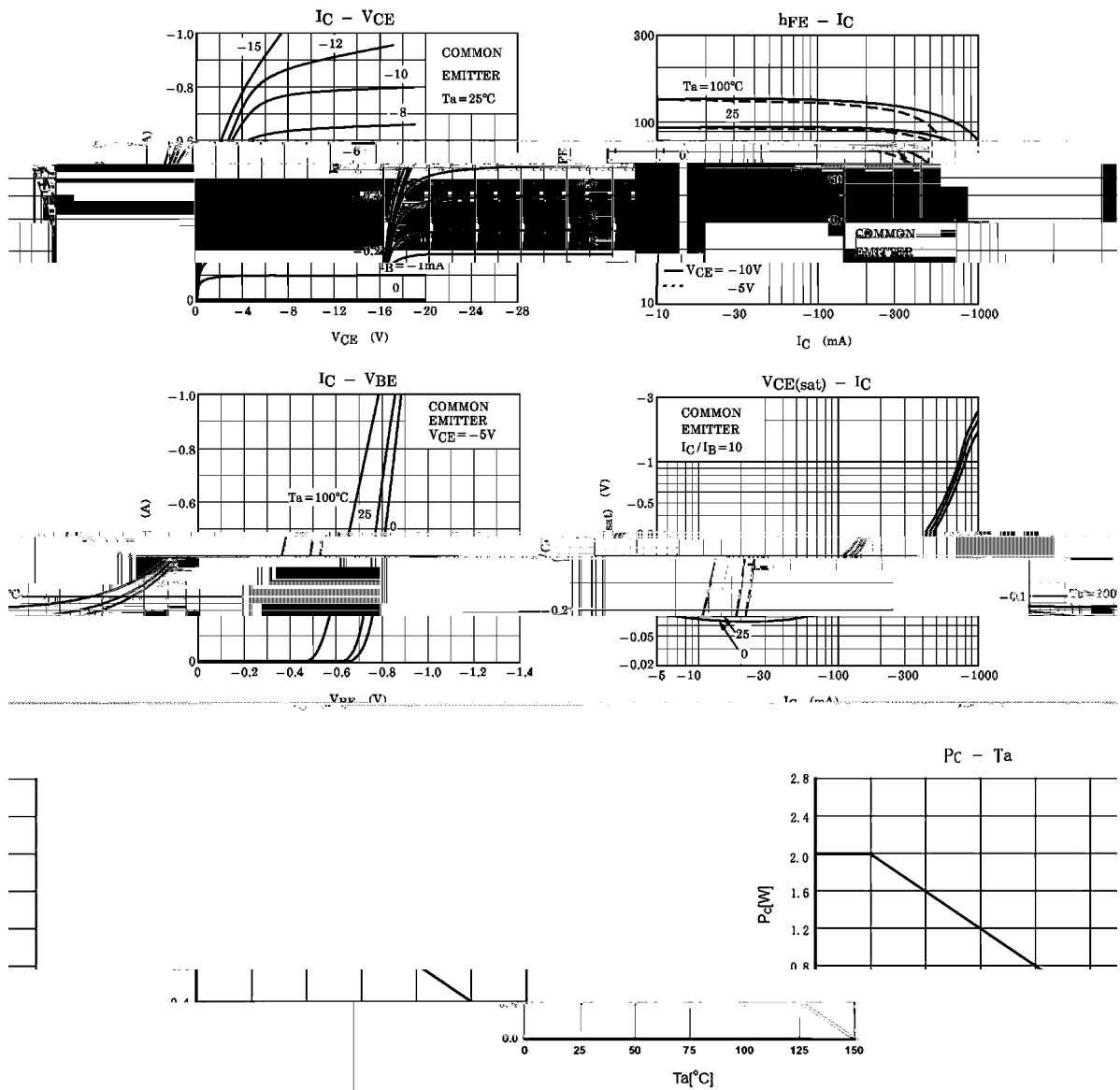
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	D	E
h_{FE} Range	60 120	100 200

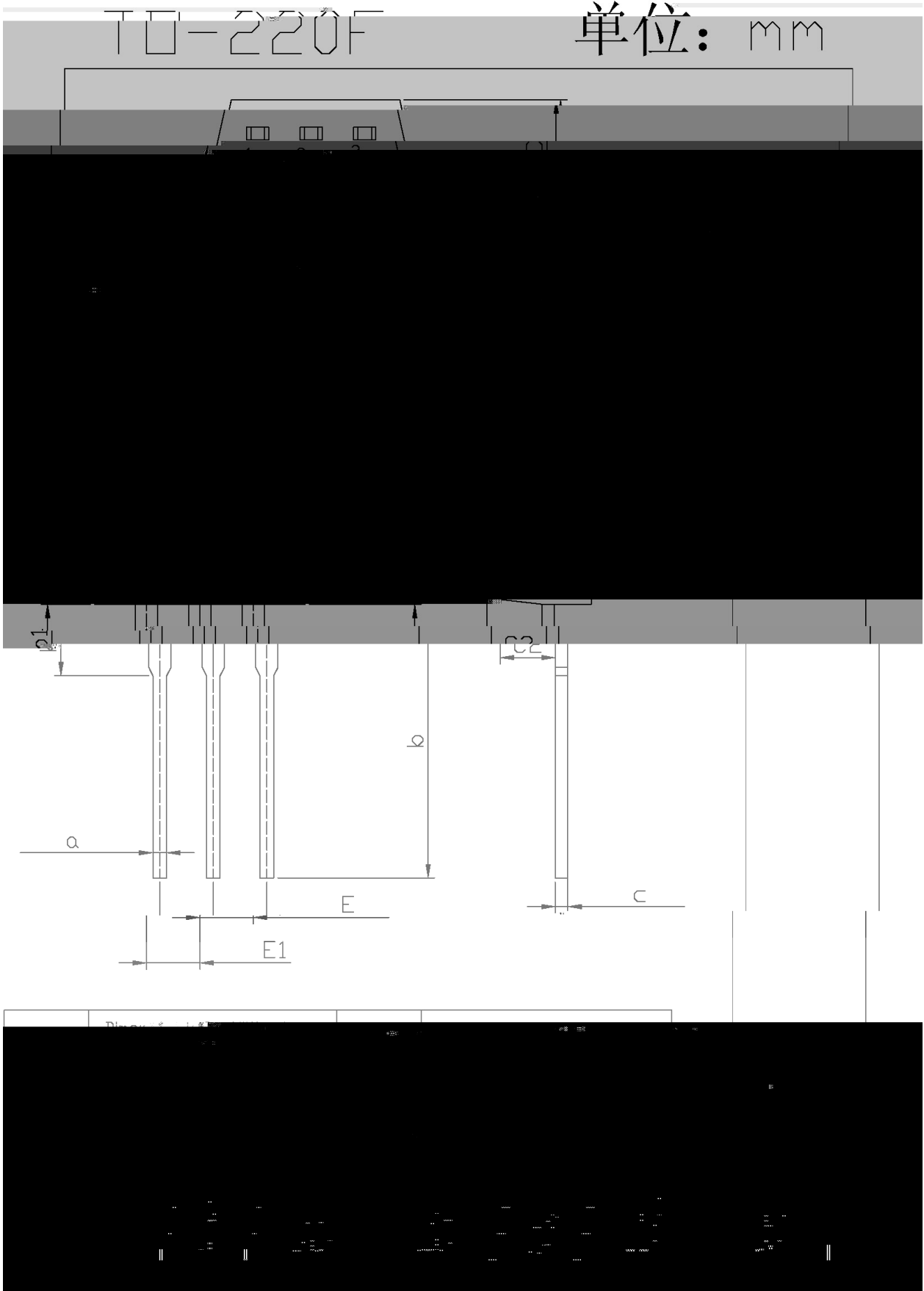
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-160	V
Collector to Emitter Voltage	V_{CEO}	-160	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-1.5	A
Collector Power Dissipation bl			WA

Collector Power Dissipation $P_{D4-286(WA)}$ JET55.62591928 481.32 0.47998 ref55.625672768 0.48 18.28

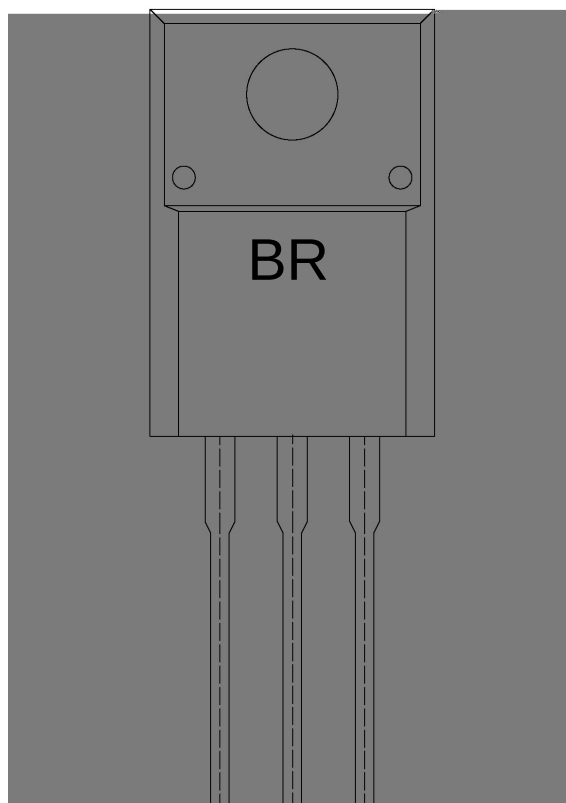
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

A1964

D: h_{FE}

Note:

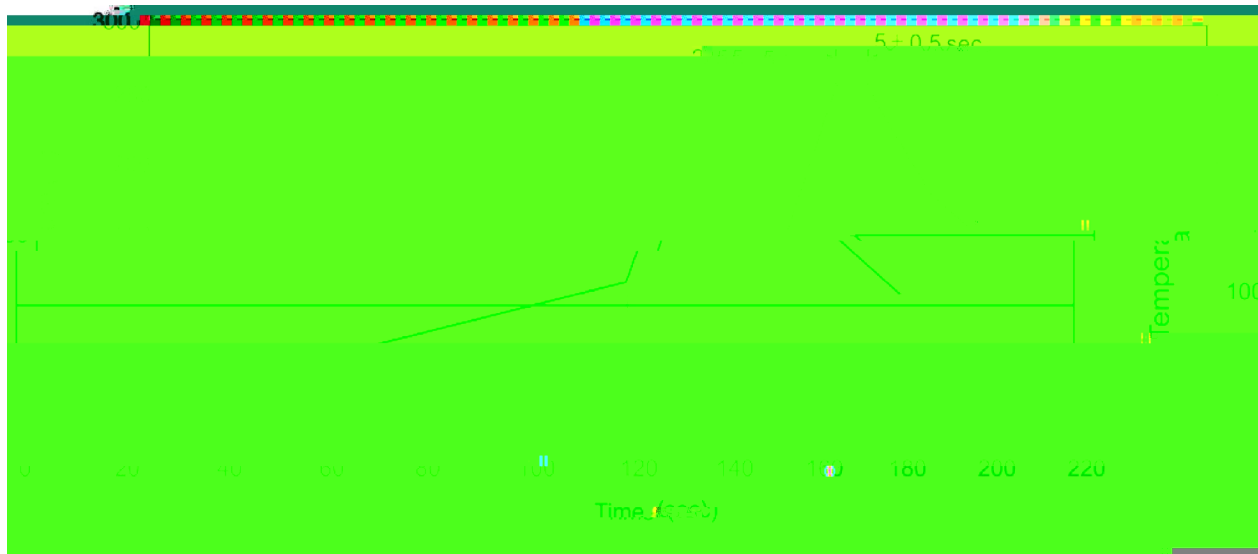
BR: Company Code.

A1964: Product Type.

D: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | | 2.Peak Temp.:255±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension (unit mm ³)		
	Units/Bag	Bags/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Bag	Inner Box	Outer Box
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

/ TUBE

Package Type	Units					Dimension (unit mm ³)			
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box	560×245×195